

GENERAL DESCRIPTION

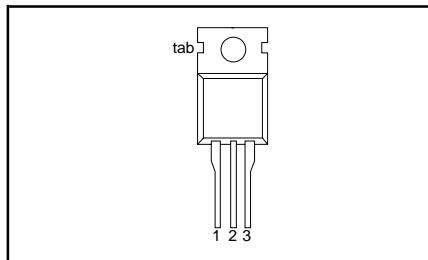
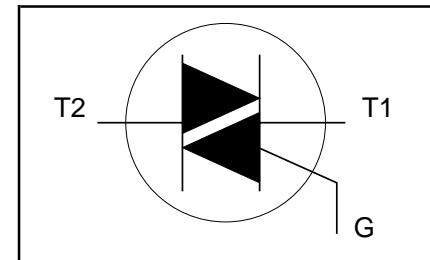
Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V_{DRM}	BTA208-	600D	-	V
$I_{T(RMS)}$	BTA208-	600E	800E	A
I_{TSM}	BTA208-	600F	800B	A
		600	800	
	Repetitive peak off-state voltages			
	RMS on-state current	8	8	
	Non-repetitive peak on-state current	65	65	

PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION

SYMBOL

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-600	-800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102^\circ C$	-	600 ¹	800	A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ C$ prior to surge $t = 20\text{ ms}$ $t = 16.7\text{ ms}$ $t = 10\text{ ms}$ $I_{TM} = 12\text{ A}; I_G = 0.2\text{ A};$ $dI_G/dt = 0.2\text{ A}/\mu s$	-	8		
I^2t dI_T/dt	I^2t for fusing Repetitive rate of rise of on-state current after triggering		-	65		A
	Peak gate current		-	72		A
I_{GM}	Peak gate voltage		-	21		A^2s
V_{GM}	Peak gate power		-	100		$\text{A}/\mu s$
P_{GM}	Average gate power	over any 20 ms period	-	2		A
$P_{G(AV)}$			-	5		V
T_{stg}	Storage temperature		-	5		W
T_j	Operating junction temperature		-	0.5		W
			-40	150		$^\circ C$
			-	125		$^\circ C$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ μs .

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\-\cdot\ mb}$	Thermal resistance junction to mounting base	full cycle	-	-	2.0	K/W
$R_{th\ j\-\cdot\ a}$	Thermal resistance junction to ambient	half cycle in free air	-	60	2.4	K/W

STATIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
I_{GT}	Gate trigger current ²	BTA208-			...D	...E	...F	
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	-	5	10	25	mA
		T2+ G+	-	-	5	10	25	mA
I_L	Latching current	T2+ G-	-	-	5	10	25	mA
		T2- G-	-	-	5	10	25	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	-	15	20	25	mA
		T2+ G+	-	-	25	30	40	mA
		T2+ G-	-	-	25	30	40	mA
V_T	On-state voltage	T2- G-	-	-	25	30	40	mA
		$I_T = 10\text{ A}$	-	1.3			1.65	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7			1.5	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}$	0.25	0.4			-	V
		$T_j = 125^\circ\text{C}$						
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$	-	0.1			0.5	mA
		$T_j = 125^\circ\text{C}$						

DYNAMIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	BTA208-	...D	...E	...F		-	V/ μs
dl_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 110^\circ\text{C}$; exponential waveform; gate open circuit	30	60	70		-	A/ms
dl_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 110^\circ\text{C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit	1.8	3.5	4.5		-	A/ms
t_{gt}	Gate controlled turn-on time	$V_{DM} = 400\text{ V}; T_j = 110^\circ\text{C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$; gate open circuit	3.5	4.5	5.5		-	A/ms

² Device does not trigger in the T2-, G+ quadrant.

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

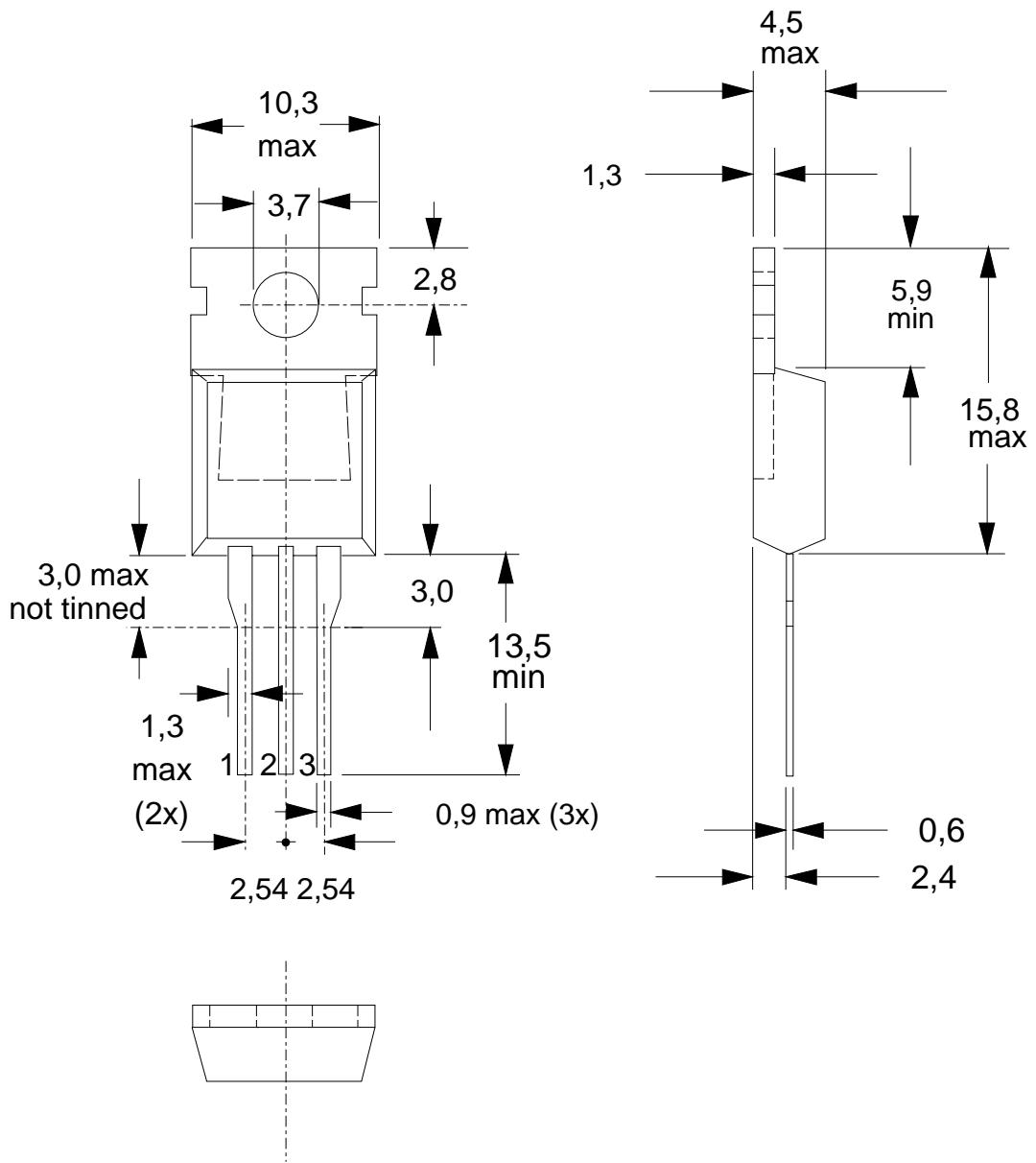


Fig.1. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)